

Silicon PNP Power Transistors

2SA1250

DESCRIPTION

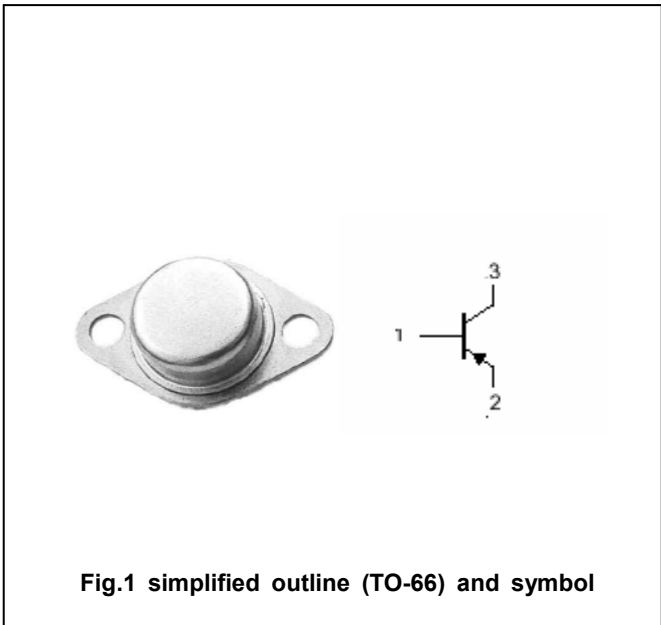
- With TO-66 package
- Excellent safe operating area
- High breakdown voltage

APPLICATIONS

- For general-purpose amplifier ;
and switching applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-200	V
V _{CEO}	Collector-emitter voltage	Open base	-200	V
V _{EBO}	Emitter-base voltage	Open collector	-7	V
I _C	Collector current		-8	A
P _D	Total power dissipation	T _C =25□	30	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA ; I _B =0	-200			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1mA ; I _C =0	-7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-5A; I _B =-0.5A			-1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-5A; I _B =-0.5A			-2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =200V; I _E =0			-10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-7V; I _C =0			-10	μA
h _{FE-1}	DC current gain	I _C =-2A ; V _{CE} =-1V	40		200	
h _{FE-2}	DC current gain	I _C =-5A ; V _{CE} =-1V	20			

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PACKAGE OUTLINE



Fig.2 outline dimensions